







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	Applicant(s): SHIMOYAMA, et al.	
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


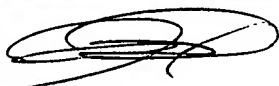
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Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA	5,003,549	Mitsui et al.	3/1991	372	46
	AB	5,465,266	Bour et al.	11/1995		
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 AE	EP 0 469 301	6/29/90	European
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	AH	Patent Abstracts of Japan; vol. 017, no. 065 (E-1317); February 9, 1993 & JP 04 269886 A (Toshiba Corp.), 9/25/92).
	AI	Patent Abstracts of Japan; vol. 1997, no. 11, November 28, 1997 & JP 09 199791 A (NNEC Corp), July 31, 1997
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Date Considered	4/5/04	